

Fabio Bernardini

PUBLICATION LIST

Book chapters

1) **Fabio Bernardini:**

Spontaneous and Piezoelectric Polarization: Basic Theory vs. Practical Recipes, in
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Regular Papers (no proceedings)

- 1) C.M. Bertoni, M. Buongiorno Nardelli, **F. Bernardini**, F. Finocchi and E. Molinari:
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- 2) C.M. Bertoni, F. Finocchi, **F. Bernardini**, M. Buongiorno Nardelli:
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- 3) M. Buongiorno Nardelli, F. Finocchi, M. Palumbo, R. De Felice, C.M. Bertoni, **F. Bernardini** and S. Ossicini:
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- 4) S. Ossicini, and **F. Bernardini:**
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- 5) A. Fasolino, S. Ossicini, **F. Bernardini:**
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- 6) **F. Bernardini**, A. Fasolino, S. Ossicini:
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- 7) S. Ossicini, A. Fasolino, and **F. Bernardini**:
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- 10) L. Dorigoni, O. Bisi, **F. Bernardini** and S. Ossicini:
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- 11) **F. Bernardini** and R. M. Nieminen:
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- 12) A. Lindell, M. Pessa, A. Salokatve, **F. Bernardini**, R.M. Nieminen, M. Paalanen:
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- 13) **F. Bernardini**, V. Fiorentini and A. Bosin:
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- 14) **F. Bernardini**, V. Fiorentini and D. Vanderbilt:
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- 15) **F. Bernardini**, V. Fiorentini and D. Vanderbilt:
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- 16) **F. Bernardini**, V. Fiorentini:
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- 17) **F. Bernardini** and V. Fiorentini:
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- 18) Antonella Fara, **F. Bernardini**, and V. Fiorentini:
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- 19) Fabio Della Sala, Aldo Di Carlo, Paolo Lugli, **Fabio Bernardini**, Vincenzo Fiorentini, Reinhard Scholz and Jean-Marc Jancu:
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- 22) **Fabio Bernardini**, Vincenzo Fiorentini:
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- 27) **Fabio Bernardini**, Vincenzo Fiorentini, and David Vanderbilt:
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- 28) Agostino Zoroddu, **Fabio Bernardini**, Paolo Ruggerone, and Vincenzo Fiorentini:
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- 30) G. Satta, G. Profeta, **F. Bernardini**, A. Continenza, and S. Massidda:
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- 32) Vincenzo Fiorentini, **Fabio Bernardini**, and Oliver Ambacher:
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- 39) **F. Bernardini**, and V. Fiorentini:
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- 40) O. Ambacher, M. Eickhoff, A. Link, M. Hermann, M. Stutzmann, **F. Bernardini**,
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- 41) **F. Bernardini**, G. Profeta, and A. Continenza:
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- 42) **F. Bernardini**, S. Picozzi, and A. Continenza: *Energetic stability and magnetic
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- 43) **F. Bernardini**, A. Mattoni, and L. Colombo:
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- 44) **F. Bernardini** and L. Colombo:
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- 45) **F. Bernardini** and S. Massidda:
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First-principle investigation of native and impurity defects in MgB₂,
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- 10) **F. Bernardini**, M. Monni, A. Sanna, Sandro Massidda: *Electronic and structural properties of LiAl co-doped MgB2*, Physica C, **460-462**, 566 (2007).

Dissertations

- 1) **F. Bernardini**, *Calcolo da Principi Primi delle Proprietà Elettroniche, Strutturali e Vibrazionali per Solidi, Superfici e Chemisorbimento Ordinato*, Tesi di Laurea, Università di Roma "Tor Vergata", 1990.
 - 2) **F. Bernardini**, *Studio da Principi Primi delle Proprietà Elettroniche di Interfacce e Sistemi Confinati basati sul Silicio*, Tesi di Dottorato di Ricerca, Università di Modena, 1994.
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